

AF
2815

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Kiyoshi IRINO

Serial No.: 09/428,052

Filed: October 27, 1999

For: METHOD OF FABRICATING A SEMICONDUCTOR DEVICE CONTAINING
NITROGEN IN A GATE OXIDE FILM (AS AMENDED)



BOX AF

Group Art Unit: 2815

Examiner: J. Diaz

8/C (M)
1/3/01
Taylor

AMENDMENT AFTER FINAL REJECTION

BOX AF

Director of Patents and Trademarks
Washington, D.C. 20231

Date: December 27, 2000

Sir:

In response to the Office Action dated December 28, 2000, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 7 without prejudice or disclaimer.

Please amend claims 6 and 8 -10 as follows:

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6. (Amended) A method of fabricating a semiconductor device, comprising the steps of:

forming a gate oxide film on a substrate;

forming a gate electrode pattern on said gate oxide film; and

introducing N atoms into said gate oxide film while using said gate electrode pattern

as a mask,

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DIAZ